

Yoshiki Saito

List of Publications by Year in descending order

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28
papers

2,005
citations

686830

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610482

24
g-index

28
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28
docs citations

28
times ranked

1498
citing authors

#	ARTICLE	IF	CITATIONS
1	Unusual properties of the fundamental band gap of InN. Applied Physics Letters, 2002, 80, 3967-3969.	1.5	1,380
2	Growth Temperature Dependence of Indium Nitride Crystalline Quality Grown by RF-MBE. Physica Status Solidi (B): Basic Research, 2002, 234, 796-800.	0.7	105
3	Growth of High-Electron-Mobility InN by RF Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2001, 40, L91-L93.	0.8	91
4	Optical Properties of In _x Ga _{1-x} N with Entire Alloy Composition on InN Buffer Layer Grown by RF-MBE. Physica Status Solidi (B): Basic Research, 2002, 234, 750-754.	0.7	65
5	MBE-growth, characterization and properties of InN and InGaN. Physica Status Solidi A, 2003, 200, 202-208.	1.7	45
6	Growth of AlN films on SiC substrates by RF-MBE and RF-MEE. Journal of Crystal Growth, 2001, 230, 392-397.	0.7	34
7	m-Plane GaInN Light Emitting Diodes Grown on Patterned a-Plane Sapphire Substrates. Applied Physics Express, 0, 2, 041001.	1.1	28
8	Low resistivity of highly Si-doped n-type Al _{0.62} Ga _{0.38} N layer by suppressing self-compensation. Applied Physics Express, 2020, 13, 025504.	1.1	28
9	m-Plane GaN Films Grown on Patterned a-Plane Sapphire Substrates with 3-inch Diameter. Applied Physics Express, 0, 2, 031002.	1.1	26
10	Efficiency improvement of AlGaN-based deep-ultraviolet light-emitting diodes and their virus inactivation application. Japanese Journal of Applied Physics, 2021, 60, 080501.	0.8	20
11	Effect of AlN buffer layer on the growth of InN epitaxial film on Si substrate. Physica Status Solidi (B): Basic Research, 2003, 240, 429-432.	0.7	19
12	Influence of substrate polarity on growth of InN films by RF-MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2810-2813.	0.8	19
13	Polarity of High-Quality Indium Nitride Grown by RF Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2001, 228, 13-16.	0.7	17
14	Reduction in operating voltage of AlGaN homojunction tunnel junction deep-UV light-emitting diodes by controlling impurity concentrations. Applied Physics Express, 2021, 14, 084001.	1.1	17
15	Recent development of InN RF-MBE growth and its structural and property characterization. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1487-1495.	0.8	16
16	Electronic degeneracy conduction in highly Si-doped Al _{0.6} Ga _{0.4} N layers based on the carrier compensation effect. Applied Physics Letters, 2020, 117, .	1.5	16
17	Effect of atomic hydrogen irradiation on native oxides of InN surface. Journal of Crystal Growth, 2002, 237-239, 1022-1026.	0.7	13
18	Sapphire substrate off-angle and off-direction dependences on characteristics of AlGaN-based deep ultraviolet light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SC1025.	0.8	12

#	ARTICLE	IF	CITATIONS
19	Origin of optical absorption in AlN with air voids. Japanese Journal of Applied Physics, 2019, 58, SCCC29.	0.8	11
20	Band-GaP Energy and Physical Properties of InN Grown by RF-Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2003, 798, 259.	0.1	8
21	Single Crystalline InN Films Grown on Si Substrates By Using A Brief Substrate Nitridation Process. Materials Research Society Symposia Proceedings, 2002, 743, L3.26.1.	0.1	6
22	Formation mechanism and suppression of Ga-rich streaks at macro-step edges in the growth of AlGaIn on an AlN/sapphire-template. Journal of Crystal Growth, 2020, 534, 125475.	0.7	6
23	Structural design optimization of 279 nm wavelength AlGaIn homojunction tunnel junction deep-UV light-emitting diode. Applied Physics Express, 2022, 15, 044003.	1.1	6
24	Study of Epitaxial Relationship in InN Growth on Sapphire (0001) by RF-MBE. Physica Status Solidi (B): Basic Research, 2001, 228, 17-20.	0.7	5
25	Effects of hydrostatic pressure on optical properties of InN and In-rich group III-nitride alloys. Physica Status Solidi (B): Basic Research, 2004, 241, 3107-3112.	0.7	5
26	Electrical Properties of InN Grown by RF-MBE. Materials Research Society Symposia Proceedings, 2000, 639, 11181.	0.1	4
27	Visualization of depletion layer in AlGaIn homojunction p-n junction. Applied Physics Express, 0, , .	1.1	3
28	Two Step Growth of InN Films on Sapphire (0001) Substrates Without Nitridation Process by RF-MBE. Materials Research Society Symposia Proceedings, 2001, 693, 477.	0.1	0